



Welcome to [E-XFL.COM](#)

What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	CANbus, LINbus, SCI, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	79
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 33x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5602df1mll3

Table 1. MPC5602D device comparison (continued)

Feature	Device			
	MPC5601DxLH	MPC5601DxLL	MPC5602DxLH	MPC5602DxLL
Debug	JTAG			
Package	64 LQFP	100 LQFP	64 LQFP	100 LQFP

¹ Refer to eMIOS chapter of device reference manual for information on the channel configuration and functions.
² Type X = MC + MCB + OPWMT + OPWMB + OPWFMB + SAIC + SAOC
³ Type Y = OPWMT + OPWMB + SAIC + SAOC
⁴ Type G = MCB + IPWM + IPM + DAOC + OPWMT + OPWMB + OPWFMB + OPWMCB + SAIC + SAOC
⁵ Type H = IPWM + IPM + DAOC + OPWMT + OPWMB + SAIC + SAOC
⁶ I/O count based on multiplexing with peripherals

2 Block diagram

Figure 1 shows a top-level block diagram of the MPC5602D device series.

Table 2. MPC5602D series block summary (continued)

Block	Function
Real-time counter (RTC)	Provides a free-running counter and interrupt generation capability that can be used for timekeeping applications
Reset generation module (MC_RGM)	Centralizes reset sources and manages the device reset sequence of the device
Static random-access memory (SRAM)	Provides storage for program code, constants, and variables
System integration unit lite (SIUL)	Provides control over all the electrical pad controls and up to 32 ports with 16 bits of bidirectional, general-purpose input and output signals and supports up to 32 external interrupts with trigger event configuration
System status and configuration module (SSCM)	Provides system configuration and status data (such as memory size and status, device mode and security status), device identification data, debug status port enable and selection, and bus and peripheral abort enable/disable
System timer module (STM)	Provides a set of output compare events to support AUTOSAR (Automotive Open System Architecture) and operating system tasks
Software watchdog timer (SWT)	Provides protection from runaway code
Wakeup unit (WKPU)	Supports up to 18 external sources that can generate interrupts or wakeup events, of which 1 can cause non-maskable interrupt requests or wakeup events.

3 Package pinouts and signal descriptions

3.1 Package pinouts

The available LQFP pinouts are provided in the following figures. For pin signal descriptions, please refer to [Table 5](#).

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function ¹	Function	Peripheral	I/O direction ²	Pad type	RESET configuration	Pin number	
								64 LQFP	100 LQFP
PB[7]	PCR[23]	AF0 AF1 AF2 AF3 —	GPIO[23] — — — ADC1_P[3]	SIUL — — — ADC	I — — — I	I	Tristate	37	55
PB[8]	PCR[24]	AF0 AF1 AF2 AF3 — —	GPIO[24] — — — ADC1_S[4] WKPU[25] ³	SIUL — — — ADC WKPU	I — — — I I	I	Tristate	30	39
PB[9]	PCR[25]	AF0 AF1 AF2 AF3 — —	GPIO[25] — — — ADC1_S[5] WKPU[26] ³	SIUL — — — ADC WKPU	I — — — I I	I	Tristate	29	38
PB[10]	PCR[26]	AF0 AF1 AF2 AF3 — —	GPIO[26] — — — ADC1_S[6] WKPU[8] ³	SIUL — — — ADC WKPU	I/O — — — I I	J	Tristate	31	40
PB[11]	PCR[27]	AF0 AF1 AF2 AF3 —	GPIO[27] E0UC[3] — CS0_0 ADC1_S[12]	SIUL eMIOS_0 — DSPI_0 ADC	I/O I/O — I/O I	J	Tristate	38	59
PB[12]	PCR[28]	AF0 AF1 AF2 AF3 —	GPIO[28] E0UC[4] — CS1_0 ADC1_X[0]	SIUL eMIOS_0 — DSPI_0 ADC	I/O I/O — O I	J	Tristate	39	61
PB[13]	PCR[29]	AF0 AF1 AF2 AF3 —	GPIO[29] E0UC[5] — CS2_0 ADC1_X[1]	SIUL eMIOS_0 — DSPI_0 ADC	I/O I/O — O I	J	Tristate	40	63
PB[14]	PCR[30]	AF0 AF1 AF2 AF3 —	GPIO[30] E0UC[6] — CS3_0 ADC1_X[2]	SIUL eMIOS_0 — DSPI_0 ADC	I/O I/O — O I	J	Tristate	41	65

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function ¹	Function	Peripheral	I/O direction ²	Pad type	RESET configuration	Pin number	
								64 LQFP	100 LQFP
PC[7]	PCR[39]	AF0 AF1 AF2 AF3 — —	GPIO[39] — — — LIN1RX WKPU[12] ³	SIUL — — — LINFlex_1 WKPU	I/O — — — I I	S	Tristate	17	26
PC[8]	PCR[40]	AF0 AF1 AF2 AF3	GPIO[40] LIN2TX E0UC[3] —	SIUL LINFlex_2 eMIOS_0 —	I/O O I/O —	S	Tristate	63	99
PC[9]	PCR[41]	AF0 AF1 AF2 AF3 — —	GPIO[41] — E0UC[7] — LIN2RX WKPU[13] ³	SIUL — eMIOS_0 — LINFlex_2 WKPU	I/O — I/O — I I	S	Tristate	2	2
PC[10]	PCR[42]	AF0 AF1 AF2 AF3	GPIO[42] — — MA[1]	SIUL — — ADC	I/O — — O	M	Tristate	13	22
PC[11]	PCR[43]	AF0 AF1 AF2 AF3 —	GPIO[43] — — MA[2] WKPU[5] ³	SIUL — — ADC WKPU	I/O — — O I	S	Tristate	—	21
PC[12]	PCR[44]	AF0 AF1 AF2 AF3 —	GPIO[44] E0UC[12] — — EIRQ[19]	SIUL eMIOS_0 — — SIUL	I/O I/O — — I	M	Tristate	—	97
PC[13]	PCR[45]	AF0 AF1 AF2 AF3	GPIO[45] E0UC[13] — —	SIUL eMIOS_0 — —	I/O I/O — —	S	Tristate	—	98
PC[14]	PCR[46]	AF0 AF1 AF2 AF3 —	GPIO[46] E0UC[14] — — EIRQ[8]	SIUL eMIOS_0 — — SIUL	I/O I/O — — I	S	Tristate	—	3
PC[15]	PCR[47]	AF0 AF1 AF2 AF3 —	GPIO[47] E0UC[15] — — EIRQ[20]	SIUL eMIOS_0 — — SIUL	I/O I/O — — I	M	Tristate	—	4

Table 5. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function ¹	Function	Peripheral	I/O direction ²	Pad type	RESET configuration	Pin number	
								64 LQFP	100 LQFP
PD[8]	PCR[56]	AF0 AF1 AF2 AF3 —	GPIO[56] — — — ADC1_P[12]	SIUL — — — ADC	I — — — I	I	Tristate	—	49
PD[9]	PCR[57]	AF0 AF1 AF2 AF3 —	GPIO[57] — — — ADC1_P[13]	SIUL — — — ADC	I — — — I	I	Tristate	—	56
PD[10]	PCR[58]	AF0 AF1 AF2 AF3 —	GPIO[58] — — — ADC1_P[14]	SIUL — — — ADC	I — — — I	I	Tristate	—	57
PD[11]	PCR[59]	AF0 AF1 AF2 AF3 —	GPIO[59] — — — ADC1_P[15]	SIUL — — — ADC	I — — — I	I	Tristate	—	58
PD[12]	PCR[60]	AF0 AF1 AF2 AF3 —	GPIO[60] CS5_0 E0UC[24] — ADC1_S[8]	SIUL DSPI_0 eMIOS_0 — ADC	I/O O I/O — I	J	Tristate	—	60
PD[13]	PCR[61]	AF0 AF1 AF2 AF3 —	GPIO[61] CS0_1 E0UC[25] — ADC1_S[9]	SIUL DSPI_1 eMIOS_0 — ADC	I/O I/O I/O — I	J	Tristate	—	62
PD[14]	PCR[62]	AF0 AF1 AF2 AF3 —	GPIO[62] CS1_1 E0UC[26] — ADC1_S[10]	SIUL DSPI_1 eMIOS_0 — ADC	I/O O I/O — I	J	Tristate	—	64
PD[15]	PCR[63]	AF0 AF1 AF2 AF3 —	GPIO[63] CS2_1 E0UC[27] — ADC1_S[11]	SIUL DSPI_1 eMIOS_0 — ADC	I/O O I/O — I	J	Tristate	—	66
Port E									

4.3.1 NVUSRO[PAD3V5V] field description

The DC electrical characteristics are dependent on the PAD3V5V bit value. [Table 7](#) shows how NVUSRO[PAD3V5V] controls the device configuration.

Table 7. PAD3V5V field description

Value ¹	Description
0	High voltage supply is 5.0 V
1	High voltage supply is 3.3 V

¹ Default manufacturing value is '1'. Value can be programmed by customer in Shadow Flash.

4.3.2 NVUSRO[OSCILLATOR_MARGIN] field description

The fast external crystal oscillator consumption is dependent on the OSCILLATOR_MARGIN bit value. [Table 8](#) shows how NVUSRO[OSCILLATOR_MARGIN] controls the device configuration.

Table 8. OSCILLATOR_MARGIN field description

Value ¹	Description
0	Low consumption configuration (4 MHz/8 MHz)
1	High margin configuration (4 MHz/16 MHz)

¹ Default manufacturing value is '1'. Value can be programmed by customer in Shadow Flash.

4.3.3 NVUSRO[WATCHDOG_EN] field description

The watchdog enable/disable configuration after reset is dependent on the WATCHDOG_EN bit value. [Table 8](#) shows how NVUSRO[WATCHDOG_EN] controls the device configuration.

Table 9. WATCHDOG_EN field description

Value ¹	Description
0	Disable after reset
1	Enable after reset

¹ Default manufacturing value is '1'. Value can be programmed by customer in Shadow Flash.

4.4 Absolute maximum ratings

Table 10. Absolute maximum ratings

Symbol		Parameter	Conditions	Value		Unit
				Min	Max	
V _{SS}	SR	Digital ground on VSS_HV pins	—	0	0	V
V _{DD}	SR	Voltage on VDD_HV pins with respect to ground (V _{SS})	—	-0.3	6.0	V
V _{SS_LV}	SR	Voltage on VSS_LV (low voltage digital supply) pins with respect to ground (V _{SS})	—	V _{SS} - 0.1	V _{SS} + 0.1	V

- Table 16 provides output driver characteristics for I/O pads when in SLOW configuration.
- Table 17 provides output driver characteristics for I/O pads when in MEDIUM configuration.

Table 15. I/O pull-up/pull-down DC electrical characteristics

Symbol	C	Parameter	Conditions ¹	Value			Unit
				Min	Typ	Max	
I _{WPU}	CC	P Weak pull-up current absolute value	V _{IN} = V _{IL} , V _{DD} = 5.0 V ± 10%	PAD3V5V = 0	10	—	150
				PAD3V5V = 1 ²	10	—	250
			V _{IN} = V _{IL} , V _{DD} = 3.3 V ± 10%	PAD3V5V = 1	10	—	150
I _{WPD}	CC	P Weak pull-down current absolute value	V _{IN} = V _{IH} , V _{DD} = 5.0 V ± 10%	PAD3V5V = 0	10	—	150
				PAD3V5V = 1 ⁽²⁾	10	—	250
			V _{IN} = V _{IH} , V _{DD} = 3.3 V ± 10%	PAD3V5V = 1	10	—	150

¹ V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = -40 to 125 °C, unless otherwise specified.

² The configuration PAD3V5 = 1 when V_{DD} = 5 V is only a transient configuration during power-up. All pads but RESET are configured in input or in high impedance state.

Table 16. SLOW configuration output buffer electrical characteristics

Symbol	C	Parameter	Conditions ¹	Value			Unit
				Min	Typ	Max	
V _{OH}	CC	P Output high level SLOW configuration	Push Pull I _{OH} = -2 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 0 (recommended)	0.8V _{DD}	—	—	V
			I _{OH} = -2 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 1 ²	0.8V _{DD}	—	—	
			I _{OH} = -1 mA, V _{DD} = 3.3 V ± 10%, PAD3V5V = 1 (recommended)	V _{DD} - 0.8	—	—	
V _{OL}	CC	P Output low level SLOW configuration	Push Pull I _{OL} = 2 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 0 (recommended)	—	—	0.1V _{DD}	V
			I _{OL} = 2 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 1 ⁽²⁾	—	—	0.1V _{DD}	
			I _{OL} = 1 mA, V _{DD} = 3.3 V ± 10%, PAD3V5V = 1 (recommended)	—	—	0.5	

¹ V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = -40 to 125 °C, unless otherwise specified

² The configuration PAD3V5 = 1 when V_{DD} = 5 V is only a transient configuration during power-up. All pads but RESET are configured in input or in high impedance state.

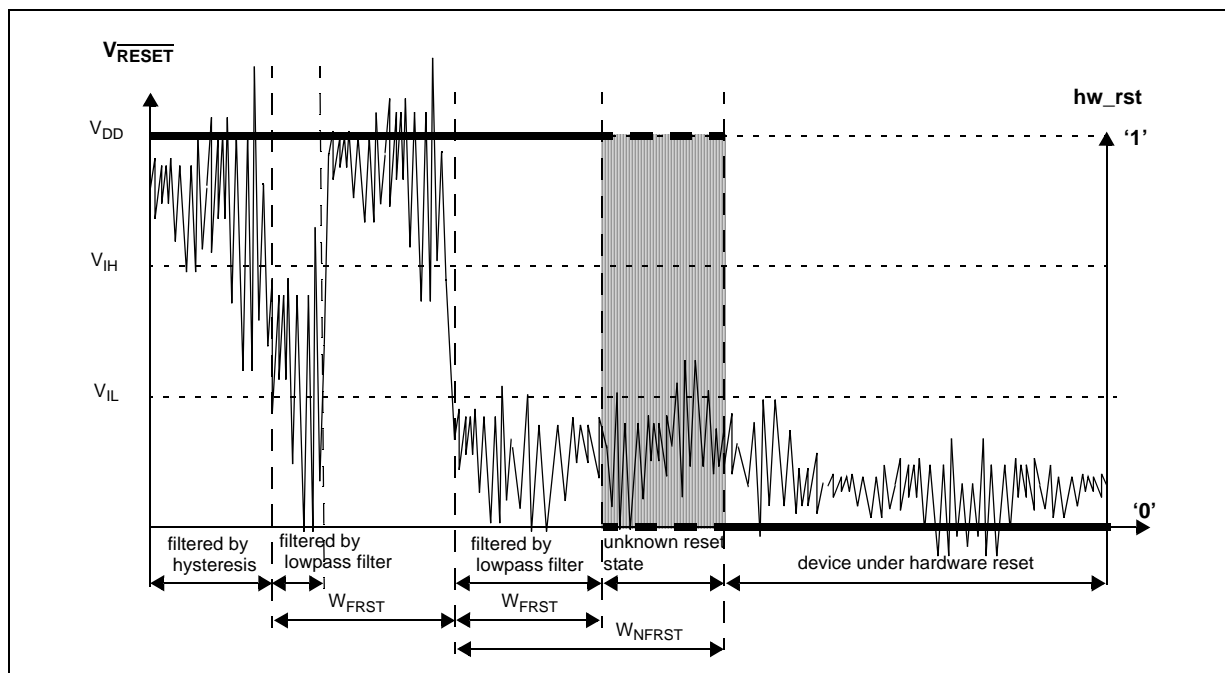


Figure 6. Noise filtering on reset signal

Table 22. Reset electrical characteristics

Symbol	C	Parameter	Conditions ¹	Value			Unit
				Min	Typ	Max	
V_{IH}	SR	P	Input High Level CMOS (Schmitt Trigger)	—	—	$0.65V_{DD}$	V
V_{IL}	SR	P	Input low Level CMOS (Schmitt Trigger)	—	—	$0.35V_{DD}$	V
V_{HYS}	CC	C	Input hysteresis CMOS (Schmitt Trigger)	—	—	$0.1V_{DD}$	V
V_{OL}	CC	P	Output low level	—	—	$0.1V_{DD}$	V
			Push Pull, $I_{OL} = 2 \text{ mA}$, $V_{DD} = 5.0 \text{ V} \pm 10\%$, $PAD3V5V = 0$ (recommended)	—	—	$0.1V_{DD}$	
			Push Pull, $I_{OL} = 1 \text{ mA}$, $V_{DD} = 5.0 \text{ V} \pm 10\%$, $PAD3V5V = 1^2$	—	—	$0.1V_{DD}$	
			Push Pull, $I_{OL} = 1 \text{ mA}$, $V_{DD} = 3.3 \text{ V} \pm 10\%$, $PAD3V5V = 1$ (recommended)	—	—	0.5	

Electrical characteristics

- LV_CFLA: Low voltage supply for code flash module. It is supplied with dedicated ballast and shorted to LV_COR through double bonding.
- LV_DFLA: Low voltage supply for data flash module. It is supplied with dedicated ballast and shorted to LV_COR through double bonding.
- LV_PLL: Low voltage supply for FMPLL. It is shorted to LV_COR through double bonding.

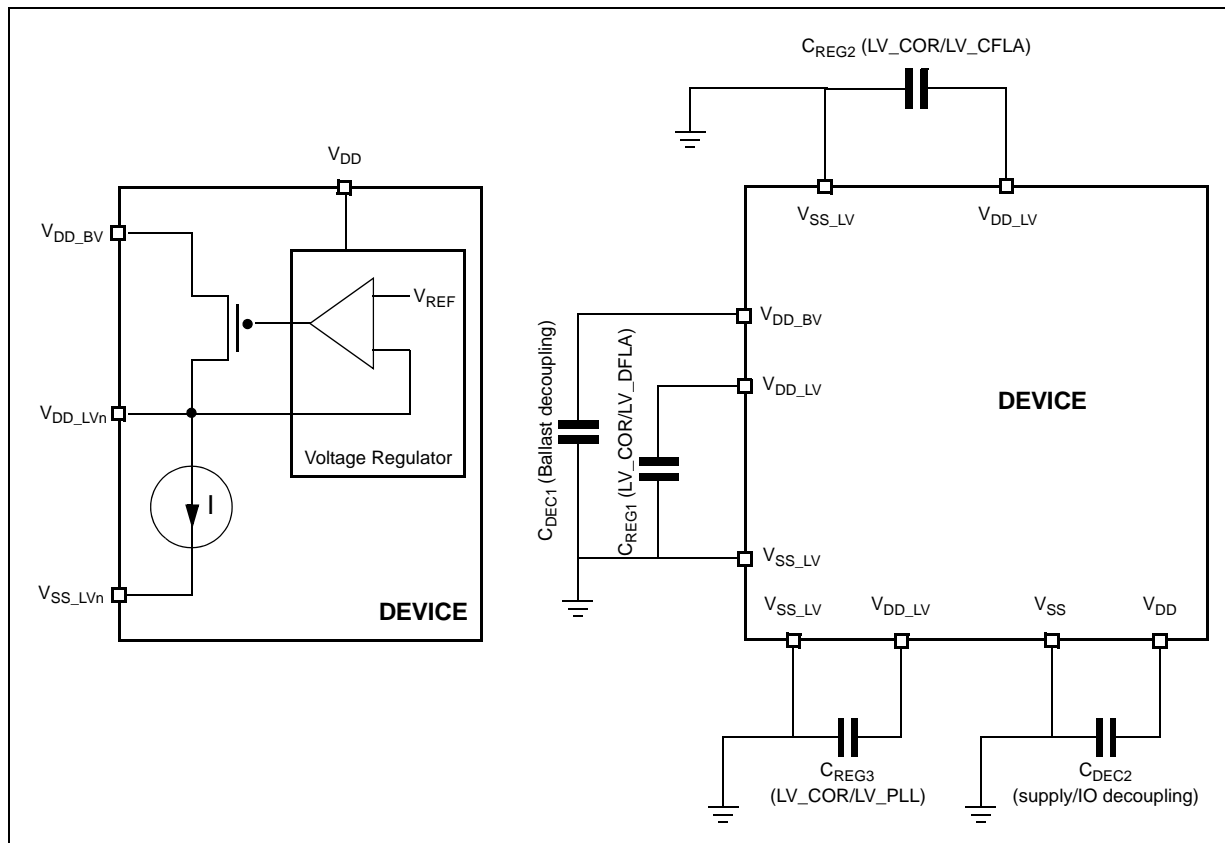


Figure 7. Voltage regulator capacitance connection

The internal voltage regulator requires external capacitance (C_{REGn}) to be connected to the device in order to provide a stable low voltage digital supply to the device. Capacitances should be placed on the board as near as possible to the associated pins. Care should also be taken to limit the serial inductance of the board to less than 5 nH.

Each decoupling capacitor must be placed between each of the three V_{DD_LV}/V_{SS_LV} supply pairs to ensure stable voltage (see [Section 4.5, Recommended operating conditions](#)).

Table 23. Voltage regulator electrical characteristics

Symbol	C	Parameter	Conditions ¹	Value			Unit
				Min	Typ	Max	
C_{REGn}	SR	Internal voltage regulator external capacitance	—	200	—	500	nF
R_{REG}	SR	Stability capacitor equivalent serial resistance	Range: 10 kHz to 20 MHz	—	—	0.2	Ω

Table 24. Low voltage detector electrical characteristics

Symbol		C	Parameter	Conditions ¹	Value			Unit
					Min	Typ	Max	
V _{PORUP}	SR	P	Supply for functional POR module	T _A = 25 °C, after trimming	1.0	—	5.5	V
V _{PORH}	CC	P	Power-on reset threshold		1.5	—	2.6	V
V _{LVDHV3H}	CC	T	LVDHV3 low voltage detector high threshold		—	—	2.95	V
V _{LVDHV3L}	CC	P	LVDHV3 low voltage detector low threshold		2.6	—	2.9	V
V _{LVDHV3BH}	CC	P	LVDHV3B low voltage detector high threshold		—	—	2.95	V
V _{LVDHV3BL}	CC	P	LVDHV3B low voltage detector low threshold		2.6	—	2.9	V
V _{LVDHV5H}	CC	T	LVDHV5 low voltage detector high threshold		—	—	4.5	V
V _{LVDHV5L}	CC	P	LVDHV5 low voltage detector low threshold		3.8	—	4.4	V
V _{LVDLVCORL}	CC	P	LVDLVCOR low voltage detector low threshold		1.08	—	1.16	V
V _{LVDLVBKPL}	CC	P	LVDLVBKP low voltage detector low threshold		1.08	—	1.16	V

¹ V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = -40 to 125 °C, unless otherwise specified

4.10 Power consumption

Table 25 provides DC electrical characteristics for significant application modes. These values are indicative values; actual consumption depends on the application.

Table 25. Power consumption on VDD_BV and VDD_HV

Symbol		C	Parameter	Conditions ¹		Value			Unit
						Min	Typ	Max	
I _{DDMAX} ²	CC	D	RUN mode maximum average current	—		—	90	130 ³	mA
I _{DDRUN} ⁴	CC	T	RUN mode typical average current ⁵	f _{CPU} = 8 MHz	—	7	—	mA	
		T		f _{CPU} = 16 MHz	—	18	—		
		T		f _{CPU} = 32 MHz	—	29	—		
		P		f _{CPU} = 48 MHz	—	40	100		
I _{DDHALT}	CC	C	HALT mode current ⁶	Slow internal RC oscillator (128 kHz) running	T _A = 25 °C	—	8	15	mA
		P			T _A = 125 °C	—	14	25	
I _{DDSTOP}	CC	P	STOP mode current ⁷	Slow internal RC oscillator (128 kHz) running	T _A = 25 °C	—	180	700 ⁸	μA
		D			T _A = 55 °C	—	500	—	
		D			T _A = 85 °C	—	1	6 ⁽⁸⁾	mA
		D			T _A = 105 °C	—	2	9 ⁽⁸⁾	
		P			T _A = 125 °C	—	4.5	12 ⁽⁸⁾	
		P							

Table 25. Power consumption on VDD_BV and VDD_HV (continued) (continued)

Symbol		C	Parameter	Conditions ¹		Value			Unit
						Min	Typ	Max	
I _{DDSTDBY}	CC	P	STANDBY mode current ⁹	Slow internal RC oscillator (128 kHz) running	T _A = 25 °C	—	30	100	μA
		D			T _A = 55 °C	—	75	—	
		D			T _A = 85 °C	—	180	700	
		D			T _A = 105 °C	—	315	1000	
		P			T _A = 125 °C	—	560	1700	

¹ V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = -40 to 125 °C, unless otherwise specified

² Running consumption does not include I/Os toggling which is highly dependent on the application. The given value is thought to be a worst case value with all peripherals running, and code fetched from code flash while modify operation ongoing on data flash. Notice that this value can be significantly reduced by application: switch off not used peripherals (default), reduce peripheral frequency through internal prescaler, fetch from RAM most used functions, use low power mode when possible.

³ Higher current may be sinked by device during power-up and standby exit. Please refer to in-rush average current on [Table 23](#).

⁴ RUN current measured with typical application with accesses on both flash memory and SRAM.

⁵ Only for the “P” classification: Code fetched from SRAM: serial IPs CAN and LIN in loop-back mode, DSPI as Master, PLL as system clock (3 × Multiplier) peripherals on (eMIOS/CTU/ADC) and running at maximum frequency, periodic SW/WDG timer reset enabled.

⁶ Data flash power down. Code flash in low power. SIRC (128 kHz) and FIRC (16 MHz) on. 10 MHz XTAL clock. FlexCAN: 0 ON (clocked but no reception or transmission). LINFlex: instances: 0, 1, 2 ON (clocked but no reception or transmission), instance: 3 clocks gated. eMIOS: instance: 0 ON (16 channels on PA[0]–PA[11] and PC[12]–PC[15]) with PWM 20 kHz, instance: 1 clock gated. DSPI: instance: 0 (clocked but no communication). RTC/API ON. PIT ON. STM ON. ADC ON but no conversion except 2 analog watchdogs.

⁷ Only for the “P” classification: No clock, FIRC (16 MHz) off, SIRC (128 kHz) on, PLL off, HPVreg off, ULPVreg/LPVreg on. All possible peripherals off and clock gated. Flash in power down mode.

⁸ When going from RUN to STOP mode and the core consumption is > 6 mA, it is normal operation for the main regulator module to be kept on by the on-chip current monitoring circuit. This is most likely to occur with junction temperatures exceeding 125 °C and under these circumstances, it is possible for the current to initially exceed the maximum STOP specification by up to 2 mA. After entering stop, the application junction temperature will reduce to the ambient level and the main regulator will be automatically switched off when the load current is below 6 mA.

⁹ Only for the “P” classification: ULPVreg on, HP/LPVreg off, 16 KB SRAM on, device configured for minimum consumption, all possible modules switched off.

4.11 Flash memory electrical characteristics

The data flash operation depends strongly on the code flash operation. If code flash is switched-off, the data flash is disabled.

4.11.1 Program/Erase characteristics

[Table 26](#) shows the program and erase characteristics.

Table 30. Flash power supply DC electrical characteristics

Symbol	C	Parameter	Conditions ¹	Value			Unit
				Min	Typ	Max	
I _{FLPW}	CC	D	Sum of the current consumption on V _{DDHV} and V _{DDBV} during flash low-power mode	—	—	910	μA
I _{CFPWD}	CC	D	Sum of the current consumption on V _{DDHV} and V _{DDBV} during flash power-down mode	Code flash	—	—	125 μA
I _{DFPWD}	CC	D		Data flash	—	—	25 μA

¹ V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = -40 to 125 °C, unless otherwise specified

4.11.3 Start-up/Switch-off timings

Table 31. Start-up time/Switch-off time

Symbol	C	Parameter	Conditions ¹	Value			Unit
				Min	Typ	Max	
t _{FLARSTEXIT}	CC	T	Delay for flash module to exit reset mode	Code flash	—	—	125 μs
				Data flash	—	—	150 μs
t _{FLALPEXIT}	CC	T	Delay for flash module to exit low-power mode ²	Code flash	—	—	0.5 μs
t _{FLAPDEXIT}	CC	T	Delay for flash module to exit power-down mode	Code flash	—	—	30 μs
				Data flash	—	—	30 ³ μs
t _{FLALPENTRY}	CC	T	Delay for flash module to enter low-power mode	Code flash	—	—	0.5 μs
t _{FLAPDENTRY}	CC	T	Delay for flash module to enter power-down mode	Code flash	—	—	1.5 μs
				Data flash	—	—	4 ⁽³⁾ μs

¹ V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = -40 to 125 °C, unless otherwise specified

² Data flash does not support low-power mode

³ If code flash is already switched-on.

4.12 Electromagnetic compatibility (EMC) characteristics

Susceptibility tests are performed on a sample basis during product characterization.

4.12.1 Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user apply EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

- Software recommendations – The software flowchart must include the management of runaway conditions such as:

4.17.2 Input impedance and ADC accuracy

In the following analysis, the input circuit corresponding to the precise channels is considered.

To preserve the accuracy of the A/D converter, it is necessary that analog input pins have low AC impedance. Placing a capacitor with good high frequency characteristics at the input pin of the device can be effective: the capacitor should be as large as possible, ideally infinite. This capacitor contributes to attenuating the noise present on the input pin; furthermore, it sources charge during the sampling phase, when the analog signal source is a high-impedance source.

A real filter can typically be obtained by using a series resistance with a capacitor on the input pin (simple RC filter). The RC filtering may be limited according to the value of source impedance of the transducer or circuit supplying the analog signal to be measured. The filter at the input pins must be designed taking into account the dynamic characteristics of the input signal (bandwidth) and the equivalent input impedance of the ADC itself.

In fact a current sink contributor is represented by the charge sharing effects with the sampling capacitance: being C_S and C_{p2} substantially two switched capacitances, with a frequency equal to the conversion rate of the ADC, it can be seen as a resistive path to ground. For instance, assuming a conversion rate of 1 MHz, with $C_S + C_{p2}$ equal to 3 pF, a resistance of 330 k Ω is obtained ($R_{EQ} = 1 / (f_c \times (C_S + C_{p2}))$), where f_c represents the conversion rate at the considered channel). To minimize the error induced by the voltage partitioning between this resistance (sampled voltage on $C_S + C_{p2}$) and the sum of $R_S + R_F$, the external circuit must be designed to respect the [Equation 4](#):

Eqn. 4

$$V_A \cdot \frac{R_S + R_F}{R_{EQ}} < \frac{1}{2} \text{LSB}$$

[Equation 4](#) generates a constraint for external network design, in particular on a resistive path.

Table 42. On-chip peripherals current consumption¹ (continued)

Symbol	C	Parameter	Conditions	Typical value ²	Unit
$I_{DD_BV(SPI)}$	CC	T SPI (DSPI) supply current on V_{DD_BV}	Ballast static consumption (only clocked)	1	μA
			Ballast dynamic consumption (continuous communication): • Baudrate: 2 Mbit/s • Transmission every 8 μs • Frame: 16 bits	$16 \times f_{periph}$	μA
$I_{DD_BV(ADC)}$	CC	T ADC supply current on V_{DD_BV}	$V_{DD} = 5.5 V$ Ballast static consumption (no conversion)	$41 \times f_{periph}$	μA
			Ballast dynamic consumption (continuous conversion) ³	$5 \times f_{periph}$	μA
$I_{DD_HV_ADC(ADC)}$	CC	T ADC supply current on $V_{DD_HV_ADC}$	$V_{DD} = 5.5 V$ Analog static consumption (no conversion)	$2 \times f_{periph}$	μA
			Analog dynamic consumption (continuous conversion)	$75 \times f_{periph} + 32$	μA
$I_{DD_HV(FLASH)}$	CC	T CFlash + DFlash supply current on V_{DD_HV}	$V_{DD} = 5.5 V$ —	8.21	mA
$I_{DD_HV(PLL)}$	CC	T PLL supply current on V_{DD_HV}	$V_{DD} = 5.5 V$ —	$30 \times f_{periph}$	μA

¹ Operating conditions: $T_A = 25^\circ C$, $f_{periph} = 8 MHz$ to 48 MHz

² f_{periph} is an absolute value.

³ During the conversion, the total current consumption is given from the sum of the static and dynamic consumption, i.e., $(41 + 5) \times f_{periph}$.

4.18.2 DSPI characteristics

Table 43. DSPI characteristics¹

No.	Symbol	C	Parameter	DSPI0/DSPI1			Unit
				Min	Typ	Max	
1	t_{SCK}	SR	D SCK cycle time	Master mode (MTFE = 0)	125	—	ns
			D Slave mode (MTFE = 0)	125	—	—	
			D Master mode (MTFE = 1)	83	—	—	
			D Slave mode (MTFE = 1)	83	—	—	
—	f_{DSPI}	SR	D DSPI digital controller frequency	—	—	f_{CPU}	MHz

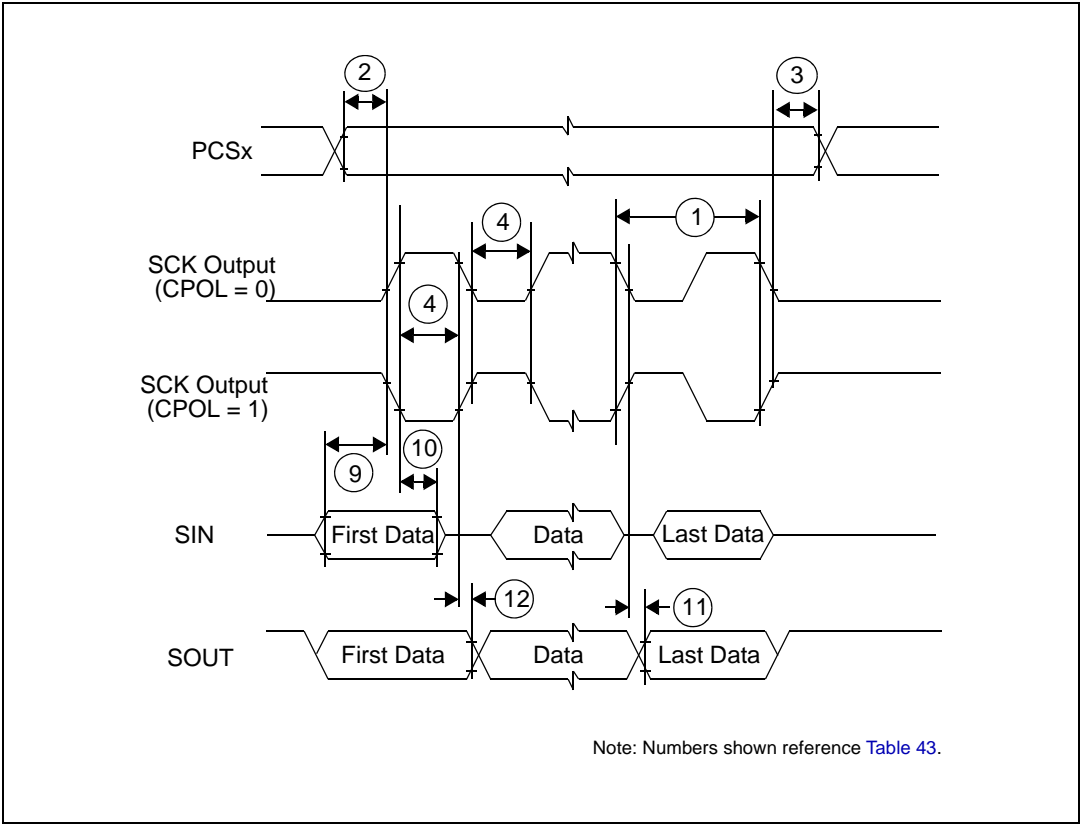


Figure 16. DSPI classic SPI timing – master, CPHA = 0

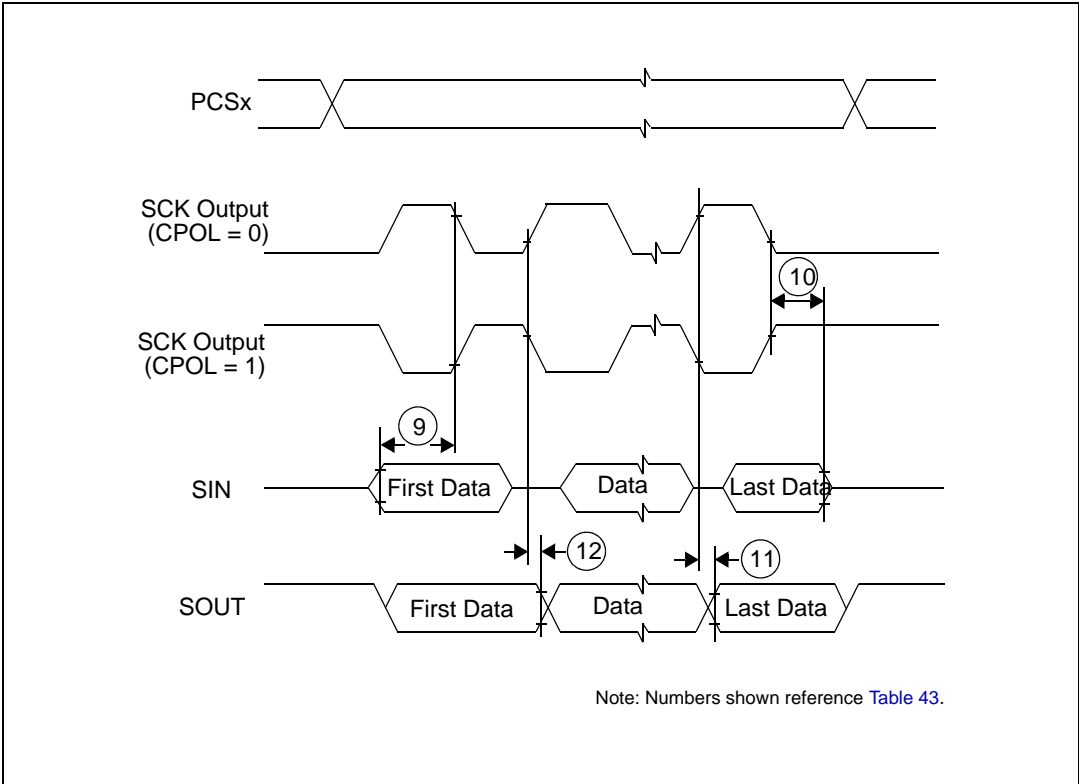


Figure 17. DSPI classic SPI timing – master, CPHA = 1

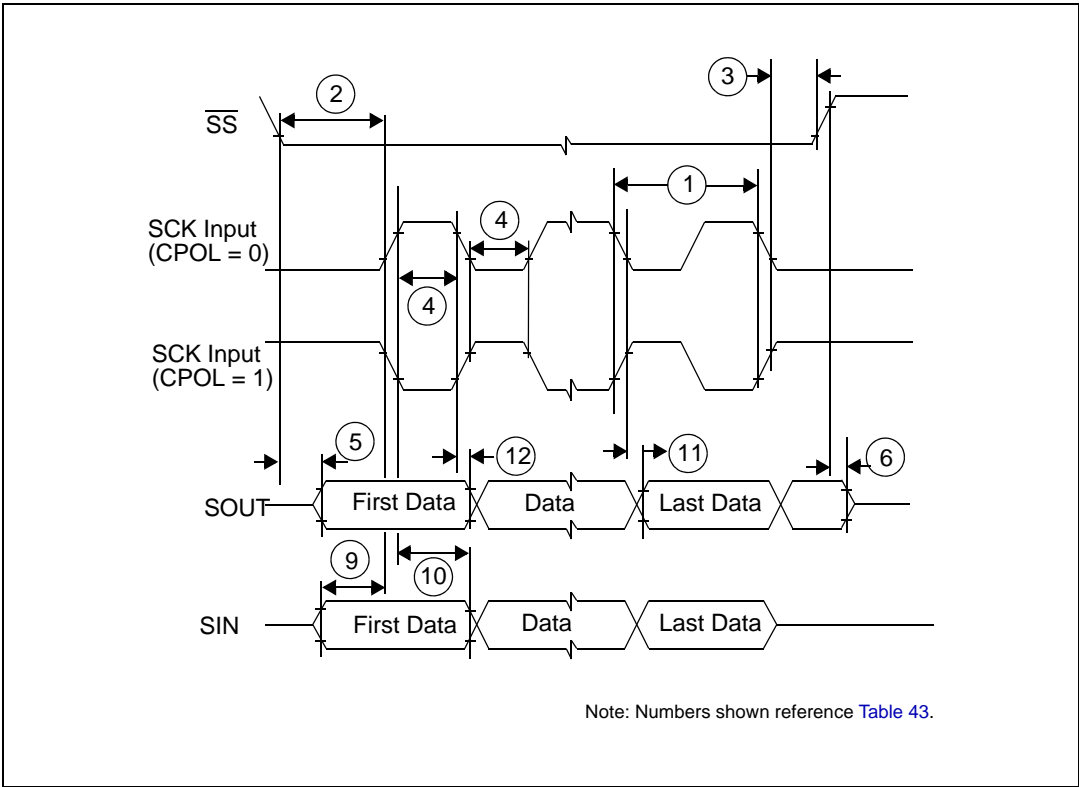


Figure 18. DSPI classic SPI timing – slave, CPHA = 0

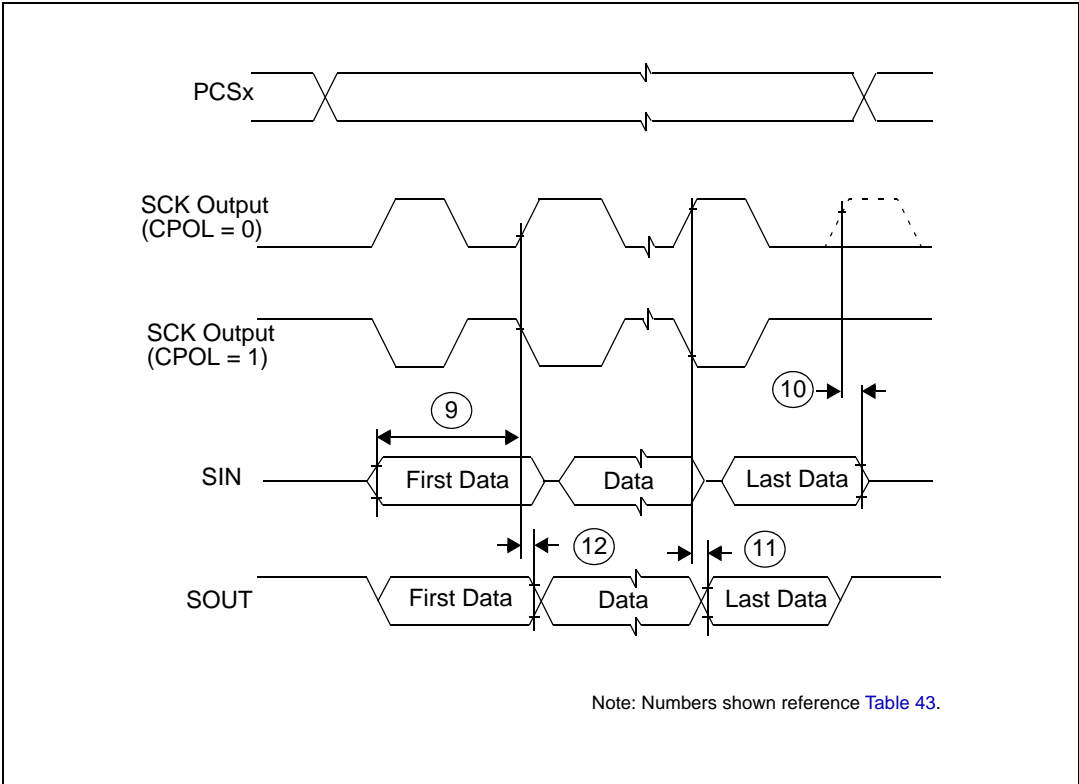


Figure 21. DSPI modified transfer format timing – master, CPHA = 1

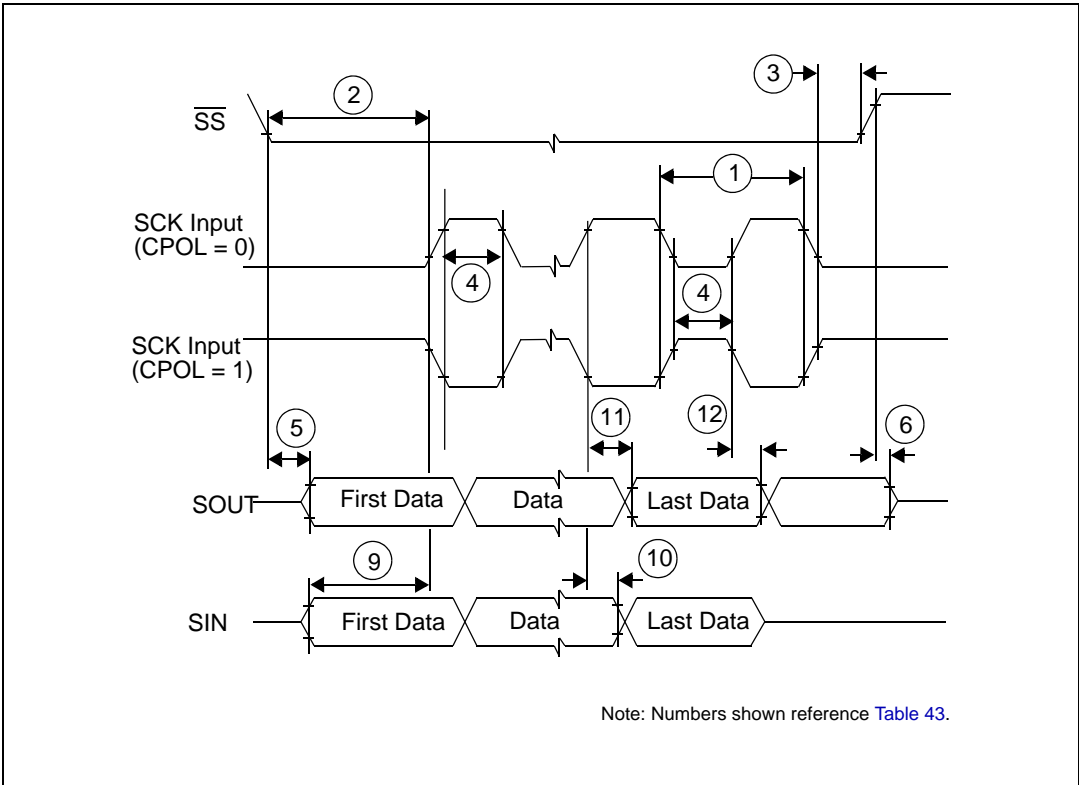


Figure 22. DSPI modified transfer format timing – slave, CPHA = 0


<div></div> <div>© FREESCALE SEMICONDUCTOR, INC. ALL RIGHTS RESERVED. ELECTRONIC VERSIONS ARE UNCONTROLLED EXCEPT WHEN ACCESSED DIRECTLY FROM THE DOCUMENT CONTROL REPOSITORY. PRINTED VERSIONS ARE UNCONTROLLED EXCEPT WHEN STAMPED "CONTROLLED COPY" IN RED.</div>	MECHANICAL OUTLINES DICTIONARY		DOCUMENT NO: 98ASS23308W	
	DO NOT SCALE THIS DRAWING		PAGE:	983
			REV:	H
<p>NOTES:</p> <p>1. ALL DIMENSIONS ARE IN MILLIMETERS.</p> <p>2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M–1994.</p> <p>3. DATUMS B, C AND D TO BE DETERMINED AT DATUM PLANE H.</p> <p>4. THE TOP PACKAGE BODY SIZE MAY BE SMALLER THAN THE BOTTOM PACKAGE SIZE BY A MAXIMUM OF 0.1 MM.</p> <p>5. DIMENSIONS DO NOT INCLUDE MOLD PROTRUSIONS. THE MAXIMUM ALLOWABLE PROTRUSION IS 0.25 mm PER SIDE. THE DIMENSIONS ARE MAXIMUM BODY SIZE DIMENSIONS INCLUDING MOLD MISMATCH.</p> <p>6. DIMENSION DOES NOT INCLUDE DAM BAR PROTRUSION. PROTRUSIONS SHALL NOT CAUSE THE LEAD WIDTH TO EXCEED 0.35. MINIMUM SPACE BETWEEN PROTRUSION AND AN ADJACENT LEAD SHALL BE 0.07 MM.</p> <p>7. DIMENSIONS ARE DETERMINED AT THE SEATING PLANE, DATUM A.</p>				
TITLE: 100 LEAD LQFP 14 X 14, 0.5 PITCH, 1.4 THICK		CASE NUMBER: 983–02		
		STANDARD: NON–JEDEC		
		PACKAGE CODE: 8264	SHEET:	3

Figure 28. 100 LQFP package mechanical drawing (Part 3 of 3)

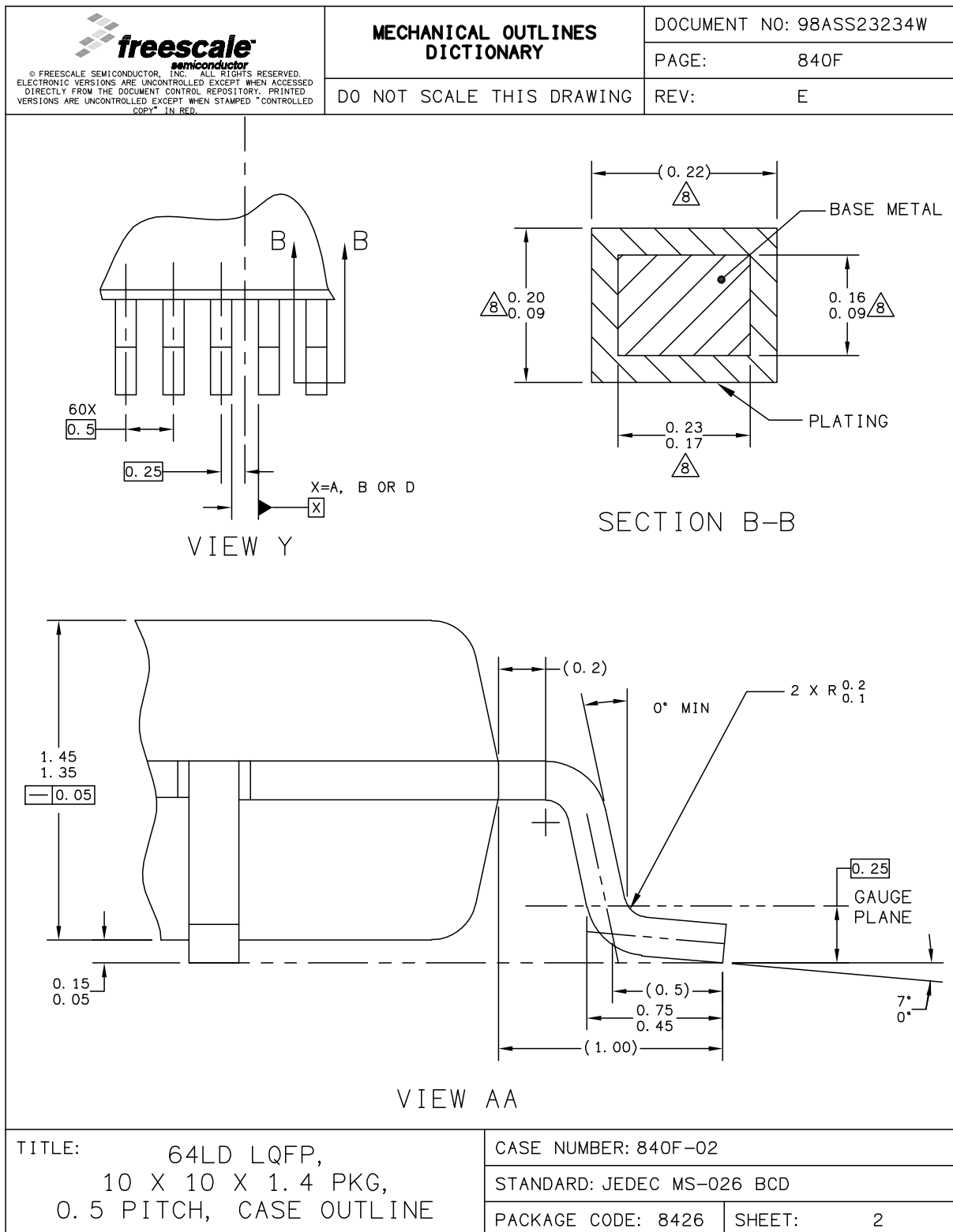


Figure 30. 64 LQFP mechanical drawing (part 2 of 3)

7 Document revision history

Table 45 summarizes revisions to this document.

Table 45. Revision history

Revision	Date	Description of Changes
1	30 Sep 2009	Initial release
2	18 Feb 2010	Updated the following tables: <ul style="list-style-type: none"> - Absolute maximum ratings - Low voltage power domain electrical characteristics; - On-chip peripherals current consumption - DSPI characteristics; - JTAG characteristics; - ADC conversion characteristics; Inserted a note on "Flash power supply DC characteristics" section.
3	10 Aug 2010	<p>"Features" section: Updated information concerning eMIOS, ADC, LINFlex, Nexus and low power capabilities</p> <p>"MPC5602D device comparison" table: updated the "Execution speed" row</p> <p>"MPC5602D series block diagram" figure:</p> <ul style="list-style-type: none"> • updated max number of Crossbar Switches • updated Legend <p>"MPC5602D series block summary" table: added contents concernig the eDMA block</p> <p>"100 LQFP pin configuration (top view)" figure:</p> <ul style="list-style-type: none"> • removed alternate functions • updated supply pins <p>"64 LQFP pin configuration (top view)" figure: removed alternate functions</p> <p>Added "Pin muxing" section</p> <p>"NVUSRO register" section: Deleted "NVUSRO[WATCHDOG_EN] field description" section</p> <p>"Recommended operating conditions (3.3 V)" table:</p> <ul style="list-style-type: none"> • V_{DD}: deleted min value • In footnote No. 3, changed capacitance value between V_{DD_BV} and V_{SS_LV} <p>"Recommended operating conditions (5.0 V)" table: deleted V_{DD} min value</p> <p>"LQFP thermal characteristics" table: changed $R_{\theta JC}$ values</p> <p>"I/O input DC electrical characteristics" table:</p> <ul style="list-style-type: none"> • W_{FI}: updated max value • W_{NFI}: updated min value <p>"I/O consumption" table: removed I_{DYNSEG} row</p> <p>Added "I/O weight" table</p> <p>"Program and erase specifications (Code Flash)" table: deleted T_{Bank_C} row</p> <p>Updated the following tables:</p> <ul style="list-style-type: none"> • "Voltage regulator electrical characteristics" • "Low voltage monitor electrical characteristics" • "Low voltage power domain electrical characteristics" • "Start-up time/Switch-off time" • "Fast external crystal oscillator (4 to 16 MHz) electrical characteristics" • "FMPLL electrical characteristics" • "Fast internal RC oscillator (16 MHz) electrical characteristics" • "ADC conversion characteristics" • "On-chip peripherals current consumption" • "DSPI characteristics" <p>"DSPI characteristics" section: removed "DSPI PCS strobe (PCSS) timing" figure</p>
3 (continued)	10 Aug 2010	"Ordering information" section: removed "Orderable part number summary" table